



SPN8910

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN8910 is the N-Channel logic enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. The SPN8910 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

FEATURES

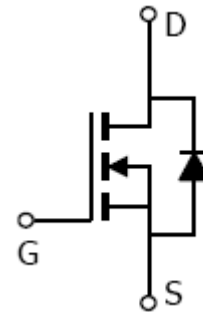
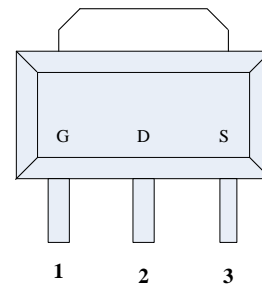
- ◆ 100V/2A, $R_{DS(ON)}= 310m\Omega@V_{GS}= 10V$
- ◆ High density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-89 package design

APPLICATIONS

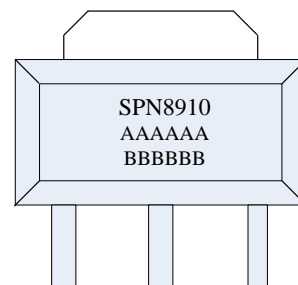
- High Frequency Small Power Switching for MB/NB/VGA
- Network DC/DC Power System
- Load Switch

PIN CONFIGURATION

SOT-89



PART MARKING





SPN8910

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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN8910S89RGB	SOT-89	SPN8910
SPN8910S89TGB	SOT-89	SPN8910

※ SPN8910S89RGB : Tape Reel ; Pb – Free ; Halogen - Free

※ SPN8910S89RGB : Tube ; Pb – Free ; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V_{DSS}	100	V	
Gate –Source Voltage	V_{GSS}	± 20	V	
Continuous Drain Current($T_J=150^{\circ}\text{C}$)	I_D	$T_A=25^{\circ}\text{C}$	2.2	A
		$T_A=70^{\circ}\text{C}$	1.7	
Pulsed Drain Current	I_{DM}	5.5	A	
Power Dissipation	P_D	1.5	W	
Operating Junction Temperature	T_J	150	$^{\circ}\text{C}$	
Storage Temperature Range	T_{STG}	-55/150	$^{\circ}\text{C}$	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	85	$^{\circ}\text{C}/\text{W}$	



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ELECTRICAL CHARACTERISTICS

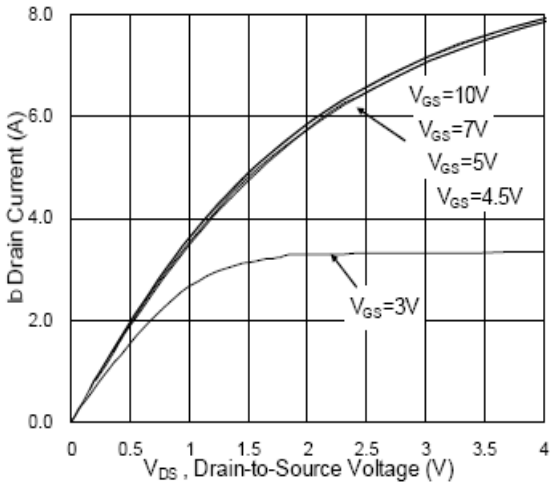
($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=125^{\circ}\text{C}$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\geq 5V, V_{GS}=10V$	2.2			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2A$		0.26	0.31	Ω
		$V_{GS}=4.5V, I_D=1A$		0.27	0.32	Ω
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=2A$		2.4		S
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$			1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=10V$ $I_D=2A$		9	13	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $f=1\text{MHz}$		508		pF
Output Capacitance	C_{oss}			29		
Reverse Transfer Capacitance	C_{rss}			16.5		
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V, I_D=2A,$ $V_{GEN}=10V, R_G=3.3\Omega$		2		nS
	t_r			21.5		
Turn-Off Time	$t_{d(off)}$			11.2		
	t_f			18.8		

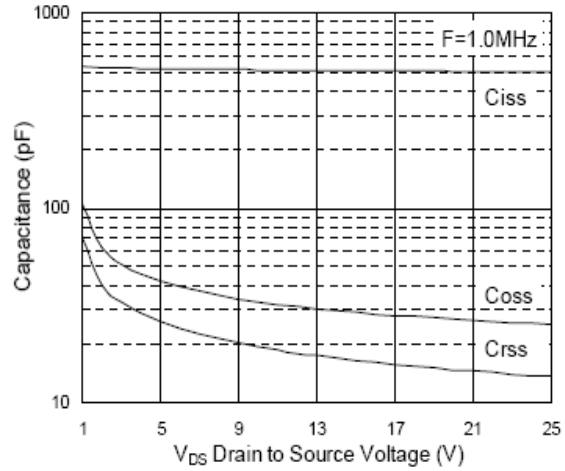


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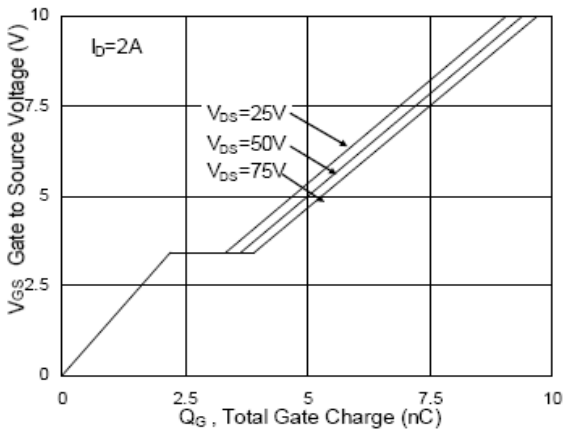
TYPICAL CHARACTERISTICS



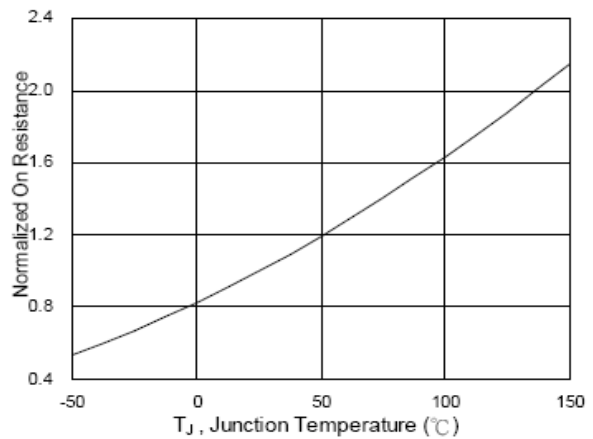
Output Characteristics



Capacitance



Gate Charge

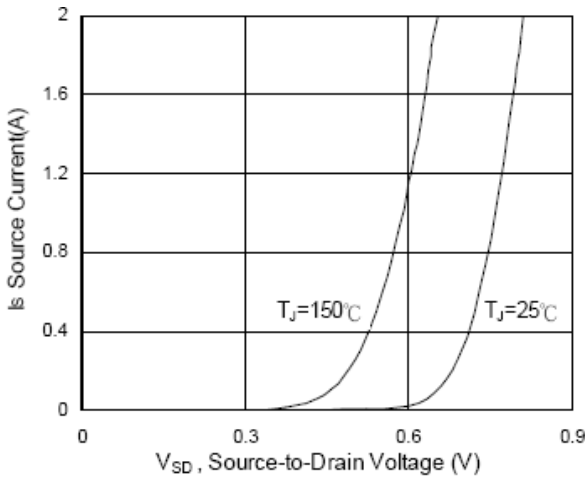


On-Resistance vs. Junction Temperature

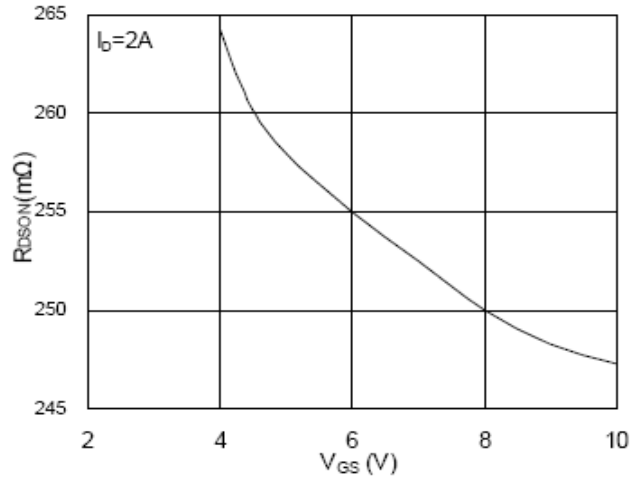


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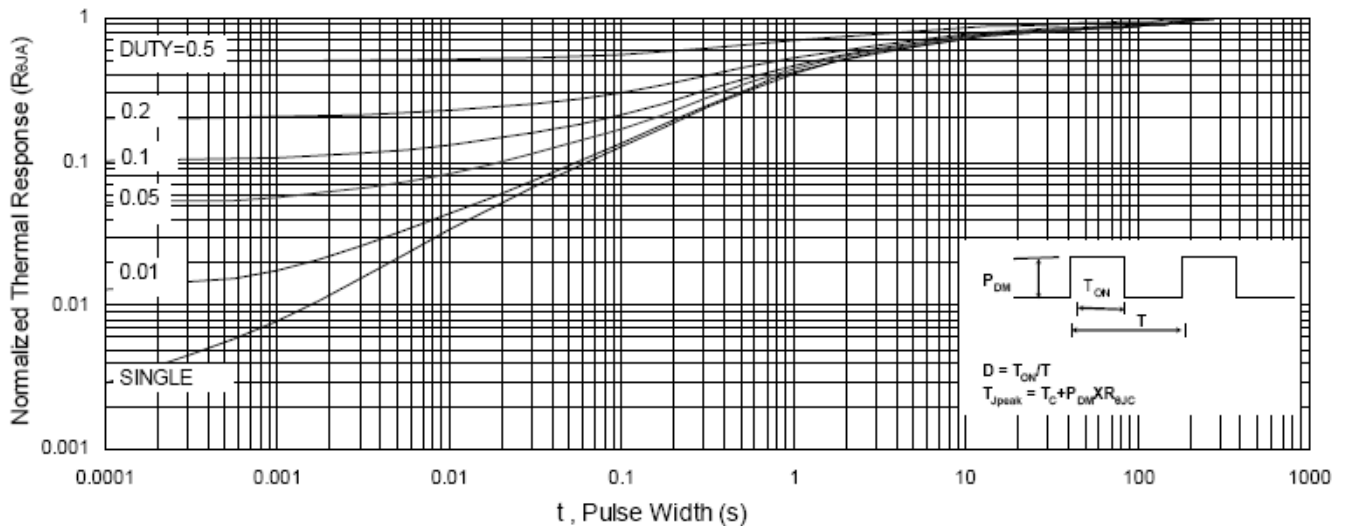
TYPICAL CHARACTERISTICS



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage



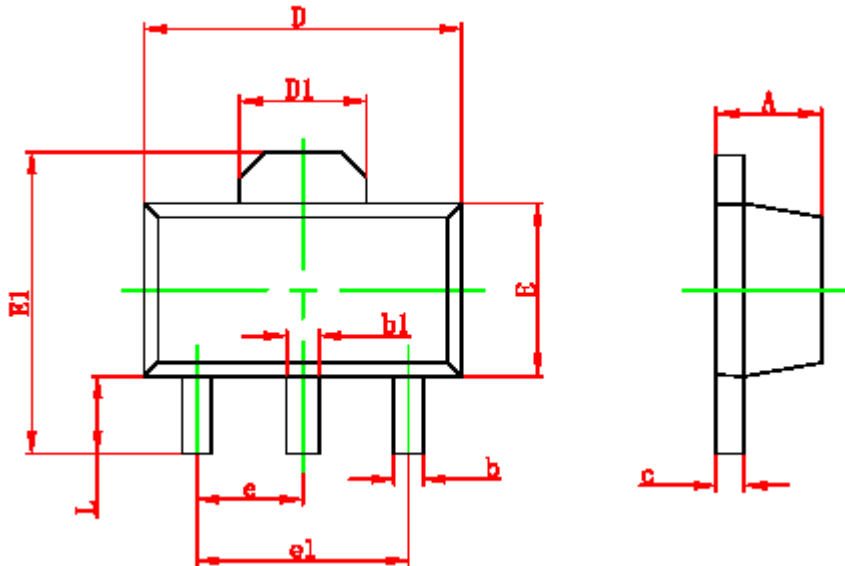
Normalized Thermal Transient Impedance, Junction to Foot



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SOT-89 PACKAGE OUTLINE



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047



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